CLAIMS

1. A wafer prober which comprises a ceramic substrate and a conductor layer formed on the surface thereof.

2. The wafer prober according to Claim 1 wherein said conductor layer is a chuck top conductor layer.

3. The wafer prober according to Claim 1 or 2 wherein said ceramic substrate is equipped with a temperature control means.

4. The wafer prober according to any of Claims 1 to 3 wherein said ceramic substrate is composed of at least one member selected from the group essentially consisting of nitride ceramics, carbide ceramics and oxide ceramics.

5. The wafer prober according to any of Claims 1 to 4 wherein said temperature control means is a Peltier device.

6. The wafer prober according to any of Claims 1 to 5 wherein said temperature control means is a heating element.

7. The wafer prober according to any of Claims 1 to 6 wherein said ceramic substrate has at least one conductor layer therein.

8. The wafer prober according to any of Claims 1 to 7 wherein said ceramic substrate is formed with a channel on its surface.

9. The wafer prober according to any of Claims 1 to 8 wherein channels are formed on the surface of said ceramic substrate, the channels being provided with air suction holes.

10. The wafer prober according to Claim 1 wherein said conductor layer is a porous layer.